

Kazuhito Tsukagoshi

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

348
papers

12,094
citations

59
h-index

97
g-index

381
ext. papers

13,152
ext. citations

5.2
avg, IF

6.28
L-index

#	Paper	IF	Citations
348	Growth and Electronic and Optoelectronic Applications of Surface Oxides on Atomically Thin WSe ₂ . <i>NIMS Monographs</i> , 2022 , 149-160	0.3	
347	Principal Component Analysis of Surface-Enhanced Raman Scattering Spectra Revealing Isomer-Dependent Electron Transport in Spiropyran Molecular Junctions: Implications for Nanoscale Molecular Electronics.. <i>ACS Omega</i> , 2022 , 7, 5578-5583	3.9	2
346	Non-invasive digital etching of van der Waals semiconductors.. <i>Nature Communications</i> , 2022 , 13, 1844	17.4	1
345	Operando hard X-ray photoelectron spectroscopy study of buried interface chemistry of Au/InO _{1.16} C _{0.04} /Al ₂ O ₃ /p+-Si stacks. <i>Applied Surface Science</i> , 2022 , 153272	6.7	0
344	Surface-Enhanced Raman Scattering Stimulated by Strong Metal-Molecule Interactions in a C Single-Molecule Junction. <i>ACS Applied Materials & Interfaces</i> , 2021 , 13, 51602-51607	9.5	1
343	Influence of adsorbed oxygen concentration on characteristics of carbon-doped indium oxide thin-film transistors under bias stress. <i>Japanese Journal of Applied Physics</i> , 2021 , 60, SCCM01	1.4	1
342	Determination of Chemical Structure of Bis(dithiolato)iron Nanosheet. <i>Chemistry Letters</i> , 2021 , 50, 576-579	1.7	5
341	Tunable Doping of Rhenium and Vanadium into Transition Metal Dichalcogenides for Two-Dimensional Electronics. <i>Advanced Science</i> , 2021 , 8, e2004438	13.6	15
340	Fabrication of WO ₃ electrochromic devices using electro-exploding wire techniques and spray coating. <i>Solar Energy Materials and Solar Cells</i> , 2021 , 223, 110960	6.4	14
339	Two-Dimensional Bis(dithiolene)iron(II) Self-Powered UV Photodetectors with Ultrahigh Air Stability. <i>Advanced Science</i> , 2021 , 8, 2100564	13.6	3
338	Water Splitting Induced by Visible Light at a Copper-Based Single-Molecule Junction. <i>Small</i> , 2021 , 17, e2008109	11	1
337	Water Splitting: Water Splitting Induced by Visible Light at a Copper-Based Single-Molecule Junction (Small 28/2021). <i>Small</i> , 2021 , 17, 2170143	11	
336	C60-Nanowire Two-State Resistance Switching Based on Fullerene Polymerization/Depolymerization. <i>ACS Applied Nano Materials</i> , 2021 , 4, 820-825	5.6	6
335	Comparison of characteristics of thin-film transistor with In ₂ O ₃ and carbon-doped In ₂ O ₃ channels by atomic layer deposition and post-metallization annealing in O ₃ . <i>Japanese Journal of Applied Physics</i> , 2021 , 60, 030903	1.4	3
334	C60-Nanowire Two-State Resistance Switching. <i>Journal of Japan Institute of Electronics Packaging</i> , 2021 , 24, 401-409	0.1	
333	Stable Resistance Switching in Lu ₃ [email[protected]]80 Nanowires Promoted by the Endohedral Effect: Implications for Single-Fullerene Motion Resistance Switching. <i>ACS Applied Nano Materials</i> , 2021 , 4, 7935-7942	5.6	0
332	Splitting charge injection for ultrahigh on/off ratio in a floating-metal-gated planar organic ferroelectric memory. <i>Materials Today Energy</i> , 2021 , 21, 100711	7	1

331	Mixed-Salt Enhanced Chemical Vapor Deposition of Two-Dimensional Transition Metal Dichalcogenides. <i>Chemistry of Materials</i> , 2021 , 33, 7301-7308	9.6	7
330	Visualizing band alignment across 2D/3D perovskite heterointerfaces of solar cells with light-modulated scanning tunneling microscopy. <i>Nano Energy</i> , 2021 , 89, 106362	17.1	3
329	On/Off Boundary of Photocatalytic Activity between Single- and Bilayer MoS. <i>ACS Nano</i> , 2020 , 14, 6663-6672	16	
328	Solution-processed organometallic quasi-two-dimensional nanosheets as a hole buffer layer for organic light-emitting devices. <i>Nanoscale</i> , 2020 , 12, 6983-6990	7.7	5
327	Feedback Electromigration Assisted by Alternative Voltage Operation for the Fabrication of Facet-Edge Nanogap Electrodes. <i>ACS Applied Nano Materials</i> , 2020 , 3, 4077-4083	5.6	3
326	Tolerance to Stretching in Thiol-Terminated Single-Molecule Junctions Characterized by Surface-Enhanced Raman Scattering. <i>Journal of Physical Chemistry Letters</i> , 2020 , 11, 6712-6717	6.4	9
325	Solution processed In-Si-O thin film transistors on hydrophilic and hydrophobic substrates. <i>Thin Solid Films</i> , 2020 , 698, 137860	2.2	5
324	Measurement of the Low-Energy Electron Inelastic Mean Free Path in Monolayer Graphene. <i>Physical Review Applied</i> , 2020 , 13,	4.3	8
323	UV degradation mechanism of TiO ₂ -based perovskite solar cells studied by pump-probe spectroscopy 2020 ,		4
322	Solution-processed organic single-crystalline semiconductors with a fence-like shape via ultrasound concussion. <i>Journal of Materials Chemistry C</i> , 2020 , 8, 2589-2593	7.1	2
321	One-Dimensional Fullerene/Porphyrin Cocrystals: Near-Infrared Light Sensing through Component Interactions. <i>ACS Applied Materials & Interfaces</i> , 2020 , 12, 2878-2883	9.5	12
320	Unravelling the origin of the photocarrier dynamics of fullerene-derivative passivation of SnO ₂ electron transporters in perovskite solar cells. <i>Journal of Materials Chemistry A</i> , 2020 , 8, 23607-23616	13	14
319	Facile and Reversible Carrier-Type Manipulation of Layered MoTe Toward Long-Term Stable Electronics. <i>ACS Applied Materials & Interfaces</i> , 2020 , 12, 42918-42924	9.5	3
318	Quantum-assisted photoelectric gain effects in perovskite solar cells. <i>NPG Asia Materials</i> , 2020 , 12,	10.3	9
317	Ab-initio investigation of preferential triangular self-formation of oxide heterostructures of monolayer [Formula: see text]. <i>Scientific Reports</i> , 2020 , 10, 21737	4.9	0
316	Observation of Plasmon Energy Gain for Emitted Secondary Electron in Vacuo. <i>Journal of Physical Chemistry Letters</i> , 2019 , 10, 5770-5775	6.4	6
315	Tunable Chemical Coupling in Two-Dimensional van der Waals Electrostatic Heterostructures. <i>ACS Nano</i> , 2019 , 13, 11214-11223	16.7	7
314	Si-incorporated amorphous indium oxide thin-film transistors. <i>Japanese Journal of Applied Physics</i> , 2019 , 58, 090506	1.4	10

313	Origin of Extended UV Stability of 2D Atomic Layer Titania-Based Perovskite Solar Cells Unveiled by Ultrafast Spectroscopy. <i>ACS Applied Materials & Interfaces</i> , 2019 , 11, 21473-21480	9.5	6
312	Effect of Bias Voltage on a Single-Molecule Junction Investigated by Surface-Enhanced Raman Scattering. <i>Journal of Physical Chemistry C</i> , 2019 , 123, 15267-15272	3.8	4
311	Identifying the molecular adsorption site of a single molecule junction through combined Raman and conductance studies. <i>Chemical Science</i> , 2019 , 10, 6261-6269	9.4	13
310	Stretch dependent electronic structure and vibrational energy of the bipyridine single molecule junction. <i>Physical Chemistry Chemical Physics</i> , 2019 , 21, 16910-16913	3.6	7
309	Near-infrared-light-induced decomposition of Rhodamine B triggered by localized surface plasmon at gold square dimers with well-defined separation distance. <i>AIP Advances</i> , 2019 , 9, 035153	1.5	1
308	Wafer-scale and deterministic patterned growth of monolayer MoS ₂ via vapor-liquid-solid method. <i>Nanoscale</i> , 2019 , 11, 16122-16129	7.7	40
307	Investigation of Ag and Cu Filament Formation Inside the Metal Sulfide Layer of an Atomic Switch Based on Point-Contact Spectroscopy. <i>ACS Applied Materials & Interfaces</i> , 2019 , 11, 27178-27182	9.5	5
306	Silicon-doped indium oxide is a promising amorphous oxide semiconductor material for thin-film transistor fabricated by spin coating method. <i>IOP Conference Series: Materials Science and Engineering</i> , 2019 , 625, 012002	0.4	2
305	Oxygen-Sensitive Layered MoTe ₂ Channels for Environmental Detection. <i>ACS Applied Materials & Interfaces</i> , 2019 , 11, 47047-47053	9.5	11
304	Selective oxidation of the surface layer of bilayer WSe ₂ by laser heating. <i>Japanese Journal of Applied Physics</i> , 2019 , 58, 120903	1.4	5
303	Characteristics of Oxide TFT Using Carbon-Doped In ₂ O ₃ Thin Film Fabricated by Low-Temperature ALD Using Ethylcyclopentadienyl Indium (EtCp) and H ₂ O & O ₃ . <i>ECS Transactions</i> , 2019 , 92, 3-13	1	5
302	Si-doping effect on solution-processed In ₂ O ₃ thin-film transistors. <i>Materials Research Express</i> , 2019 , 6, 026410	1.7	1
301	Reversible and Precisely Controllable p/n-Type Doping of MoTe ₂ Transistors through Electrothermal Doping. <i>Advanced Materials</i> , 2018 , 30, e1706995	24	44
300	Unveiling the piezoelectric nature of polar phase P(VDF-TrFE) at quasi-two-dimensional limit. <i>Scientific Reports</i> , 2018 , 8, 532	4.9	11
299	Carrier polarity engineering in carbon nanotube field-effect transistors by induced charges in polymer insulator. <i>Applied Physics Letters</i> , 2018 , 112, 013501	3.4	8
298	Pronounced photogating effect in atomically thin WSe ₂ with a self-limiting surface oxide layer. <i>Applied Physics Letters</i> , 2018 , 112, 181902	3.4	23
297	Fullerene/cobalt porphyrin charge-transfer cocrystals: Excellent thermal stability and high mobility. <i>Nano Research</i> , 2018 , 11, 1917-1927	10	20
296	Self-Assembly Atomic Stacking Transport Layer of 2D Layered Titania for Perovskite Solar Cells with Extended UV Stability. <i>Advanced Energy Materials</i> , 2018 , 8, 1701722	21.8	41

295	Photochemical Reaction Using Aminobenzenethiol Single Molecular Junction. <i>E-Journal of Surface Science and Nanotechnology</i> , 2018 , 16, 137-141	0.7	2
294	Reliability of Al ₂ O ₃ /In-Si-O-C Thin-Film Transistors with an Al ₂ O ₃ Passivation Layer under Gate-Bias Stress. <i>ECS Transactions</i> , 2018 , 86, 135-145	1	4
293	Thermal robustness evaluation of nonvolatile memory using Pt nanogaps. <i>Applied Physics Express</i> , 2018 , 11, 085202	2.4	3
292	Investigation on solution-processed In-Si-O thin-film transistor via spin-coating method 2018 ,		1
291	Solvent-Mediated Shape Engineering of Fullerene (C ₆₀) Polyhedral Microcrystals. <i>Chemistry of Materials</i> , 2018 , 30, 7146-7153	9.6	30
290	Effect of carbon doping on threshold voltage and mobility of In-Si-O thin-film transistors. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2018 , 36, 061206	1.3	4
289	Dependence of Stretch Length on Electrical Conductance and Electronic Structure of the Benzenedithiol Single Molecular Junction. <i>E-Journal of Surface Science and Nanotechnology</i> , 2018 , 16, 145-149	0.7	1
288	Layer-by-Layer Oxidation Induced Electronic Properties in Transition-Metal Dichalcogenides. <i>Journal of Physical Chemistry C</i> , 2018 , 122, 17001-17007	3.8	10
287	In situ observation of the formation process for free-standing Au nanowires with a scanning electron microscope. <i>Nanotechnology</i> , 2017 , 28, 105707	3.4	2
286	Amorphous In-Si-O Films Fabricated via Solution Processing. <i>Journal of Electronic Materials</i> , 2017 , 46, 3610-3614	1.9	7
285	Virtual substrate method for nanomaterials characterization. <i>Nature Communications</i> , 2017 , 8, 15629	17.4	17
284	Correlation between active layer thickness and ambient gas stability in IGZO thin-film transistors. <i>Journal Physics D: Applied Physics</i> , 2017 , 50, 025102	3	3
283	Controlling the thermoelectric effect by mechanical manipulation of the electron's quantum phase in atomic junctions. <i>Scientific Reports</i> , 2017 , 7, 7949	4.9	10
282	Radial Interference Contrast in in-situ SEM Observation of Metal Oxide Semiconductor Film Crystallization. <i>Microscopy and Microanalysis</i> , 2017 , 23, 1512-1513	0.5	
281	Gap width-independent spectra in 4-aminothiophenol surface enhanced Raman scattering stimulated in Au-gap array. <i>Japanese Journal of Applied Physics</i> , 2017 , 56, 065202	1.4	3
280	Two-dimensional MoTe ₂ materials: From synthesis, identification, and charge transport to electronics applications. <i>Japanese Journal of Applied Physics</i> , 2016 , 55, 1102A1	1.4	11
279	High-performance non-volatile field-effect transistor memories using an amorphous oxide semiconductor and ferroelectric polymer. <i>Journal of Materials Chemistry C</i> , 2016 , 4, 7917-7923	7.1	14
278	Highly stable, extremely high-temperature, nonvolatile memory based on resistance switching in polycrystalline Pt nanogaps. <i>Scientific Reports</i> , 2016 , 6, 34961	4.9	8

277	Hunting for Monolayer Oxide Nanosheets and Their Architectures. <i>Scientific Reports</i> , 2016 , 6, 19402	4.9	18
276	Determination of the number of atoms present in nano contact based on shot noise measurements with highly stable nano-fabricated electrodes. <i>Nanotechnology</i> , 2016 , 27, 295203	3.4	2
275	Self-Limiting Oxides on WSe ₂ as Controlled Surface Acceptors and Low-Resistance Hole Contacts. <i>Nano Letters</i> , 2016 , 16, 2720-7	11.5	90
274	Improvement of the effective work function and transmittance of thick indium tin oxide/ultrathin ruthenium doped indium oxide bilayers as transparent conductive oxide. <i>Thin Solid Films</i> , 2016 , 598, 126-130	2.3	2
273	Site-Selection in Single-Molecule Junction for Highly Reproducible Molecular Electronics. <i>Journal of the American Chemical Society</i> , 2016 , 138, 1294-300	16.4	69
272	Charge transport and mobility engineering in two-dimensional transition metal chalcogenide semiconductors. <i>Chemical Society Reviews</i> , 2016 , 45, 118-51	58.5	311
271	Self-powered graphene thermistor. <i>Nano Energy</i> , 2016 , 26, 586-594	17.1	21
270	Phase transitions from semiconductive amorphous to conductive polycrystalline in indium silicon oxide thin films. <i>Applied Physics Letters</i> , 2016 , 109, 221903	3.4	11
269	Anomalous behavior of 1/f noise in graphene near the charge neutrality point. <i>Applied Physics Letters</i> , 2016 , 108, 103106	3.4	8
268	Homogeneous double-layer amorphous Si-doped indium oxide thin-film transistors for control of turn-on voltage. <i>Journal of Applied Physics</i> , 2016 , 120, 045702	2.5	16
267	Carrier Polarity Control in WTe_2 Schottky Junctions Based on Weak Fermi-Level Pinning. <i>ACS Applied Materials & Interfaces</i> , 2016 , 8, 14732-9	9.5	52
266	Prospectively of Carbon-Doped Indium-Tungsten-Oxide Channel TFT for Bias Stress Instability. <i>ECS Transactions</i> , 2016 , 75, 149-156	1	5
265	Dopant selection for control of charge carrier density and mobility in amorphous indium oxide thin-film transistors: Comparison between Si- and W-dopants. <i>Applied Physics Letters</i> , 2015 , 106, 042106	3.4	45
264	Suppression of excess oxygen for environmentally stable amorphous In-Si-O thin-film transistors. <i>Applied Physics Letters</i> , 2015 , 106, 192103	3.4	22
263	Parity effect of bipolar quantum Hall edge transport around graphene antidots. <i>Scientific Reports</i> , 2015 , 5, 11723	4.9	6
262	Double resonance Raman modes in monolayer and few-layer MoTe ₂ . <i>Physical Review B</i> , 2015 , 91,	3.3	76
261	Edge mixing dynamics in graphene p-n junctions in the quantum Hall regime. <i>Nature Communications</i> , 2015 , 6, 8066	17.4	26
260	Reduction of the interfacial trap density of indium-oxide thin film transistors by incorporation of hafnium and annealing process. <i>AIP Advances</i> , 2015 , 5, 017116	1.5	11

259	Carrier Injection and Scattering in Atomically Thin Chalcogenides. <i>Journal of the Physical Society of Japan</i> , 2015 , 84, 121011	1.5	4
258	Solution-assembled nanowires for high performance flexible and transparent solar-blind photodetectors. <i>Journal of Materials Chemistry C</i> , 2015 , 3, 596-600	7.1	37
257	Nanocontact Disorder in Nanoelectronics for Modulation of Light and Gas Sensitivities. <i>Scientific Reports</i> , 2015 , 5, 13035	4.9	8
256	Codoping of zinc and tungsten for practical high-performance amorphous indium-based oxide thin film transistors. <i>Journal of Applied Physics</i> , 2015 , 118, 125702	2.5	21
255	Influence of Al ₂ O ₃ layer insertion on the electrical properties of Ga-In-Zn-O thin-film transistors. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2015 , 33, 061506	2.9	6
254	Reducing contact resistance in ferroelectric organic transistors by buffering the semiconductor/dielectric interface. <i>Applied Physics Letters</i> , 2015 , 107, 053304	3.4	17
253	Origin of Noise in Layered MoTe ₂ Transistors and its Possible Use for Environmental Sensors. <i>Advanced Materials</i> , 2015 , 27, 6612-9	24	58
252	Electrostatically Reversible Polarity of Ambipolar δ -MoTe ₂ Transistors. <i>ACS Nano</i> , 2015 , 9, 5976-83	16.7	89
251	Wafer-scale fabrication of transistors using CVD-grown graphene and its application to inverter circuit. <i>Japanese Journal of Applied Physics</i> , 2015 , 54, 04DN06	1.4	4
250	Self-limiting layer-by-layer oxidation of atomically thin WSe ₂ . <i>Nano Letters</i> , 2015 , 15, 2067-73	11.5	153
249	Boost up carrier mobility for ferroelectric organic transistor memory via buffering interfacial polarization fluctuation. <i>Scientific Reports</i> , 2014 , 4, 7227	4.9	57
248	Patterning technology for solution-processed organic crystal field-effect transistors. <i>Science and Technology of Advanced Materials</i> , 2014 , 15, 024203	7.1	33
247	Highly stable Au atomic contacts covered with benzenedithiol under ambient conditions. <i>Physical Chemistry Chemical Physics</i> , 2014 , 16, 15662-6	3.6	8
246	Barrier inhomogeneities at vertically stacked graphene-based heterostructures. <i>Nanoscale</i> , 2014 , 6, 795-797	9.7	56
245	Electrostatically Reversible Polarity of Dual-Gated Graphene Transistors. <i>IEEE Nanotechnology Magazine</i> , 2014 , 13, 1039-1043	2.6	12
244	Semiconducting properties of bilayer graphene modulated by an electric field for next-generation atomic-film electronics. <i>Journal Physics D: Applied Physics</i> , 2014 , 47, 094003	3	7
243	Strong enhancement of Raman scattering from a bulk-inactive vibrational mode in few-layer MoTe ₂ . <i>ACS Nano</i> , 2014 , 8, 3895-903	16.7	223
242	Structure and transport properties of the interface between CVD-grown graphene domains. <i>Nanoscale</i> , 2014 , 6, 7288-94	7.7	42

241	Strain-tunable superconducting field-effect transistor with an organic strongly-correlated electron system. <i>Advanced Materials</i> , 2014 , 26, 3490-5	24	23
240	Influence of Al ₂ O ₃ Gate Dielectric on Transistor Properties for IGZO Thin Film Transistor. <i>ECS Transactions</i> , 2014 , 61, 345-351	1	2
239	Stable amorphous In ₂ O ₃ -based thin-film transistors by incorporating SiO ₂ to suppress oxygen vacancies. <i>Applied Physics Letters</i> , 2014 , 104, 102103	3-4	70
238	Low-temperature processable amorphous In-W-O thin-film transistors with high mobility and stability. <i>Applied Physics Letters</i> , 2014 , 104, 152103	3-4	67
237	Modulation of effective damping constant using spin Hall effect. <i>Applied Physics Letters</i> , 2014 , 104, 092408	3-4	30
236	Controllable film densification and interface flatness for high-performance amorphous indium oxide based thin film transistors. <i>Applied Physics Letters</i> , 2014 , 105, 163503	3-4	9
235	Spin injection and detection in a graphene lateral spin valve using an yttrium-oxide tunneling barrier. <i>Applied Physics Express</i> , 2014 , 7, 085101	2-4	6
234	Self-formed copper oxide contact interlayer for high-performance oxide thin film transistors. <i>Applied Physics Letters</i> , 2014 , 105, 023503	3-4	11
233	Ambipolar MoTe ₂ transistors and their applications in logic circuits. <i>Advanced Materials</i> , 2014 , 26, 3263-9	2-4	308
232	Thickness scaling effect on interfacial barrier and electrical contact to two-dimensional MoS ₂ layers. <i>ACS Nano</i> , 2014 , 8, 12836-42	16.7	129
231	Large [6,6]-phenyl C ₆₁ butyric acid methyl (PCBM) hexagonal crystals grown by solvent-vapor annealing. <i>Materials Chemistry and Physics</i> , 2014 , 145, 327-333	4-4	13
230	Control of molecular orientation and morphology in organic bilayer solar cells: Copper phthalocyanine on gold nanodots. <i>Thin Solid Films</i> , 2014 , 562, 467-470	2.2	8
229	Metal atomic contacts under defined environmental conditions. <i>Transactions of the Materials Research Society of Japan</i> , 2014 , 39, 225-229	0.2	
228	Thickness-dependent interfacial Coulomb scattering in atomically thin field-effect transistors. <i>Nano Letters</i> , 2013 , 13, 3546-52	11.5	236
227	Rational design of a high performance all solid state flexible micro-supercapacitor on paper. <i>RSC Advances</i> , 2013 , 3, 15827	3-7	40
226	Low-cost fully transparent ultraviolet photodetectors based on electrospun ZnO-SnO ₂ heterojunction nanofibers. <i>Advanced Materials</i> , 2013 , 25, 4625-30	24	243
225	High-performance top-gated monolayer SnS ₂ field-effect transistors and their integrated logic circuits. <i>Nanoscale</i> , 2013 , 5, 9666-70	7-7	226
224	On practical charge injection at the metal/organic semiconductor interface. <i>Scientific Reports</i> , 2013 , 3, 1026	4-9	59

223	Suppression of thermally activated carrier transport in atomically thin MoS ₂ on crystalline hexagonal boron nitride substrates. <i>Nanoscale</i> , 2013 , 5, 9572-6	7.7	60
222	Epitaxial Growth and Electronic Properties of Large Hexagonal Graphene Domains on Cu(111) Thin Film. <i>Applied Physics Express</i> , 2013 , 6, 075101	2.4	65
221	Self-aligned formation of sub 1 nm gaps utilizing electromigration during metal deposition. <i>ACS Applied Materials & Interfaces</i> , 2013 , 5, 12869-75	9.5	22
220	Self-assembly of semiconductor/insulator interfaces in one-step spin-coating: a versatile approach for organic field-effect transistors. <i>Physical Chemistry Chemical Physics</i> , 2013 , 15, 7917-33	3.6	47
219	Realization of graphene field-effect transistor with high- κ Ca ₂ Nb ₃ O ₁₀ nanoflake as top-gate dielectric. <i>Applied Physics Letters</i> , 2013 , 103, 023113	3.4	10
218	Understanding Thickness-Dependent Charge Transport in Pentacene Transistors by Low-Frequency Noise. <i>IEEE Electron Device Letters</i> , 2013 , 34, 1298-1300	4.4	16
217	Flexible SnO ₂ hollow nanosphere film based high-performance ultraviolet photodetector. <i>Chemical Communications</i> , 2013 , 49, 3739-41	5.8	85
216	Structural and charge transport characteristics of graphene layers obtained from CVD thin film and bulk graphite materials. <i>Carbon</i> , 2013 , 52, 49-55	10.4	9
215	In situ purification to eliminate the influence of impurities in solution-processed organic crystals for transistor arrays. <i>Journal of Materials Chemistry C</i> , 2013 , 1, 1352-1358	7.1	31
214	Conduction tuning of graphene based on defect-induced localization. <i>ACS Nano</i> , 2013 , 7, 5694-700	16.7	69
213	Contact Thickness Effects in Bottom-Contact Coplanar Organic Field-Effect Transistors. <i>IEEE Electron Device Letters</i> , 2013 , 34, 535-537	4.4	11
212	How small the contacts could be optimal for nanoscale organic transistors?. <i>Organic Electronics</i> , 2013 , 14, 1797-1804	3.5	16
211	Effects of dopants in InO _x -based amorphous oxide semiconductors for thin-film transistor applications. <i>Applied Physics Letters</i> , 2013 , 103, 172105	3.4	88
210	Joule's law for organic transistors exploration: Case of contact resistance. <i>Journal of Applied Physics</i> , 2013 , 113, 064507	2.5	19
209	Thin-film transistors fabricated by low-temperature process based on Ga- and Zn-free amorphous oxide semiconductor. <i>Applied Physics Letters</i> , 2013 , 102, 102101	3.4	55
208	Current on-off operation of graphene transistor with dual gates and He ion irradiated channel. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2013 , 10, 1608-1611		4
207	Flexible field-effect transistor arrays with patterned solution-processed organic crystals. <i>AIP Advances</i> , 2013 , 3, 052123	1.5	18
206	Large plate-like organic crystals from direct spin-coating for solution-processed field-effect transistor arrays with high uniformity. <i>Organic Electronics</i> , 2012 , 13, 264-272	3.5	65

205	Solution-processed organic crystals for field-effect transistor arrays with smooth semiconductor/dielectric interface on paper substrates. <i>Organic Electronics</i> , 2012 , 13, 815-819	3.5	58
204	Forming semiconductor/dielectric double layers by one-step spin-coating for enhancing the performance of organic field-effect transistors. <i>Organic Electronics</i> , 2012 , 13, 1146-1151	3.5	33
203	Controlled self-assembly of organic semiconductors for solution-based fabrication of organic field-effect transistors. <i>Advanced Materials</i> , 2012 , 24, 299-306	24	96
202	Gate-Controlled PIN Junction Switching Device with Graphene Nanoribbon. <i>Applied Physics Express</i> , 2012 , 5, 015101	2.4	15
201	Single-crystalline nanogap electrodes: enhancing the nanowire-breakdown process with a gaseous environment. <i>ACS Applied Materials & Interfaces</i> , 2012 , 4, 5542-6	9.5	12
200	Direct formation of organic semiconducting single crystals by solvent vapor annealing on a polymer base film. <i>Journal of Materials Chemistry</i> , 2012 , 22, 8462		52
199	Concerted Chemical-Mechanical Reaction in Catalyzed Growth of Confined Graphene Layers into Hexagonal Disks. <i>Journal of Physical Chemistry C</i> , 2012 , 116, 9106-9113	3.8	1
198	Evaluation of Spin Hall Angle and Spin Diffusion Length by Using Spin Current-Induced Ferromagnetic Resonance. <i>Applied Physics Express</i> , 2012 , 5, 073002	2.4	121
197	Origin of the relatively low transport mobility of graphene grown through chemical vapor deposition. <i>Scientific Reports</i> , 2012 , 2, 337	4.9	148
196	Controllable gallium melt-assisted interfacial graphene growth on silicon carbide. <i>Diamond and Related Materials</i> , 2012 , 24, 34-38	3.5	7
195	Tunable contact resistance in double-gate organic field-effect transistors. <i>Organic Electronics</i> , 2012 , 13, 1583-1588	3.5	15
194	Observation of Tunneling Current in Semiconducting Graphene p-n Junctions. <i>Journal of the Physical Society of Japan</i> , 2012 , 81, 014708	1.5	8
193	Controlling the crystal formation in solution-process for organic field-effect transistors with high-performance. <i>Organic Electronics</i> , 2012 , 13, 2975-2984	3.5	17
192	Quantitative Raman spectrum and reliable thickness identification for atomic layers on insulating substrates. <i>ACS Nano</i> , 2012 , 6, 7381-8	16.7	274
191	Solution-processed, Self-organized Organic Single Crystal Arrays with Controlled Crystal Orientation. <i>Scientific Reports</i> , 2012 , 2, 393	4.9	80
190	Liquid phase growth of graphene on silicon carbide. <i>Carbon</i> , 2012 , 50, 5076-5084	10.4	14
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15	Transport properties in artificial lateral superlattice. <i>Superlattices and Microstructures</i> , 1994 , 16, 295-301	2.8	15
14	Angular distribution of emitted electrons from wire by magnetic electron focusing effect and low field magnetoresistance. <i>Solid State Communications</i> , 1994 , 92, 413-417	1.6	1
13	Investigation of ballistic elastic scattering length and specularly in multiterminal GaAs/AlGaAs by magnetic electron focusing effect. <i>Applied Physics Letters</i> , 1993 , 62, 1609-1611	3.4	12
12	Influence of gate voltage on nonlocal resistance in GaAs/AlGaAs heterostructure at high magnetic fields. <i>Physica B: Condensed Matter</i> , 1993 , 184, 21-25	2.8	3
11	Role of edge and bulk currents through a gate barrier in nonlocal resistance of GaAs/Al _x Ga _{1-x} As. <i>Physical Review B</i> , 1992 , 46, 5016-5019	3.3	8
10	Nonlocal quantum conduction and the influence of contact resistance in GaAs/AlGaAs wires. <i>Surface Science</i> , 1992 , 267, 282-285	1.8	14
9	Ballistic and elastic mean free paths determined by magnetic electron focusing effect in GaAs/AlGaAs. <i>Solid State Communications</i> , 1992 , 83, 775-777	1.6	3
8	Spin-Dependent Nonlocal Quantum Transport Influenced by Gate Voltage in GaAs/AlGaAs Wires 1992 , 199-204		

7	Influence of edge current and contact on nonlocal Shubnikov-de Haas oscillations in macroscopic GaAs/AlGaAs wire. <i>Solid State Communications</i> , 1991 , 80, 571-574	1.6	16
6	Nonlocal Shubnikov-de Haas oscillations through edge and bulk currents in GaAs/AlGaAs mesoscopic quantum wires. <i>Solid State Communications</i> , 1991 , 80, 797-800	1.6	13
5	A search for multiplicity fluctuations in high energy nucleus-nucleus collisions. <i>Physics Letters, Section B: Nuclear, Elementary Particle and High-Energy Physics</i> , 1990 , 252, 303-310	4.2	33
4	An emulsion study of ^{16}O and ^{32}S interactions at 200 GeV per nucleon selected by transverse energy. <i>Nuclear Physics B</i> , 1990 , 342, 279-301	2.8	10
3	The production of charmed particles in high-energy ^{16}O -emulsion central interactions. <i>Physics Letters, Section B: Nuclear, Elementary Particle and High-Energy Physics</i> , 1989 , 224, 441-444	4.2	11
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